Silicon Controlled Rectifiers

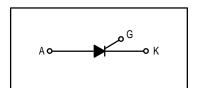
Reverse Blocking Triode Thyristors

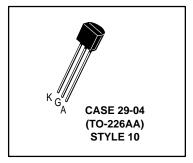
Annular PNPN devices designed for low cost, high volume consumer applications such as relay and lamp drivers, small motor controls, gate drivers for larger thyristors, and sensing and detection circuits. Supplied in an inexpensive plastic TO-226AA package which is readily adaptable for use in automatic insertion equipment.

- Sensitive Gate Trigger Current 200 μA Maximum
- Low Reverse and Forward Blocking Current 100 μ A Maximum, $T_C = 85^{\circ}C$
- Low Holding Current 5 mA Maximum
- · Passivated Surface for Reliability and Uniformity

MCR102 MCR103

SCRs 0.8 AMPERES RMS 30 and 60 VOLTS





MAXIMUM RATINGS (T_J = 25°C unless otherwise noted.)

Rating	Symbol	Value	Unit	
Peak Repetitive Forward and Reverse Blocking Voltage(2) $(T_C = + 85^{\circ}C, R_{GK} = 1 \text{ k}\Omega) \\ \text{MCR102} \\ \text{MCR103}$	VDRM VRRM	30 60	Volts	
Forward Current RMS (See Figures 1 & 2) (All Conduction Angles)	IT(RMS)	0.8	Amps	
Peak Forward Surge Current, T _A = 25°C (1/2 Cycle, Sine Wave, 60 Hz)	ITSM	10	Amps	
Circuit Fusing Considerations (t = 8.3 ms)	l ² t	0.415	A ² s	
Peak Gate Power — Forward, T _A = 25°C	P _{GM}	0.1	Watt	
Average Gate Power — Forward, T _A = 25°C	PGF(AV)	0.01	Watt	
Peak Gate Current — Forward, T _A = 25°C (300 µs, 120 PPS)	IGFM	1	Amp	
Peak Gate Voltage — Reverse	VGRM	4	Volts	
Operating Junction Temperature Range @ Rated V _{RRM} and V _{DRM}	TJ	-40 to +85	°C	
Storage Temperature Range	T _{stg}	-40 to +150	°C	
Lead Solder Temperature (< 1/16" from case, 10 s max)	_	+ 230	°C	

- 1. Temperature reference point for all case temperature is center of flat portion of package. ($T_C = +85^{\circ}C$ unless otherwise noted.)
- 2. V_{DRM} and V_{RRM} for all types can be applied on a continuous dc basis without incurring damage. Ratings apply for zero or negative gate voltage but positive gate voltage shall not be applied concurrently with a negative potential on the anode. When checking forward or reverse blocking capability, thyristor devices should not be tested with a constant current source in a manner that the voltage applied exceeds the rated blocking voltage.



MCR102 MCR103

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Case	$R_{ heta JC}$	75	°C/W
Thermal Resistance, Junction to Ambient	$R_{ heta JA}$	200	°C/W

ELECTRICAL CHARACTERISTICS (T $_{C}$ = 25°C, R $_{GK}$ = 1000 Ω unless otherwise specified.)

Characteristic		Symbol	Min	Max	Unit
Peak Forward or Reverse Blocking Current (V _{AK} = Rated V _{DRM} or V _{RRM})	T _C = 25°C T _C = 85°C	IDRM, IRRM	_	10 100	μΑ μΑ
Forward "On" Voltage ⁽¹⁾ (I _{TM} = 1 A Peak @ T _A = 25°C)		VTM	_	1.7	Volts
Gate Trigger Current (Continuous dc) ⁽²⁾ (Anode Voltage = 7 Vdc, R _L = 100 Ohms)	T _C = 25°C	lGT	_	200	μΑ
Gate Trigger Voltage (Continuous dc) (Anode Voltage = 7 Vdc, R _L = 100 Ohms)	T _C = 25°C T _C = -65°C T _C = 85°C	V _{GT} V _{GD}	— — 0.1	0.8 1.2 —	Volts
Holding Current (Anode Voltage = 7 Vdc, initiating current = 20 mA)	$T_C = 25^{\circ}C$ $T_C = -65^{\circ}C$	lн	_	5 10	mA

^{1.} Forward current applied for 1 ms maximum duration, duty cycle ≤ 1%.

FIGURE 1 – CURRENT DERATING (REFERENCE: CASE TEMPERATURE)

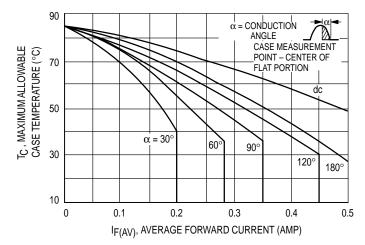
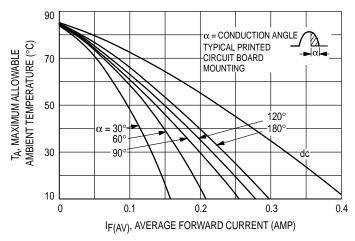
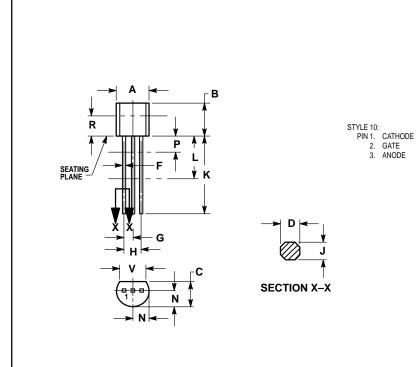


FIGURE 2 – CURRENT DERATING (REFERENCE: AMBIENT TEMPERATURE)



^{2.} $R_{\mbox{GK}}$ current is not included in measurement.

PACKAGE DIMENSIONS



- NOTES:
 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
 2. CONTROLLING DIMENSION: INCH.
 3. CONTOUR OF PACKAGE BEYOND DIMENSION R IS UNCONTROLLED.
 4. DIMENSION F APPLIES BETWEEN P AND L. DIMENSION D AND J APPLY BETWEEN L AND K MINIMUM. LEAD DIMENSION IS UNCONTROLLED IN P AND BEYOND DIMENSION K MINIMUM.

	INCHES		MILLIMETERS		
DIM	MIN	MAX	MIN	MAX	
Α	0.175	0.205	4.45	5.20	
В	0.170	0.210	4.32	5.33	
С	0.125	0.165	3.18	4.19	
D	0.016	0.022	0.41	0.55	
F	0.016	0.019	0.41	0.48	
G	0.045	0.055	1.15	1.39	
Н	0.095	0.105	2.42	2.66	
J	0.015	0.020	0.39	0.50	
K	0.500		12.70		
L	0.250		6.35		
N	0.080	0.105	2.04	2.66	
Р		0.100		2.54	
R	0.115		2.93		
٧	0.135		3.43		

CASE 29-04 (TO-226AA)

MCR102 MCR103

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